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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, I²C, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	79
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 28x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5604bavll6

1 Introduction

1.1 Document overview

This document describes the features of the family and options available within the family members, and highlights important electrical and physical characteristics of the device. To ensure a complete understanding of the device functionality, refer also to the device reference manual and errata sheet.

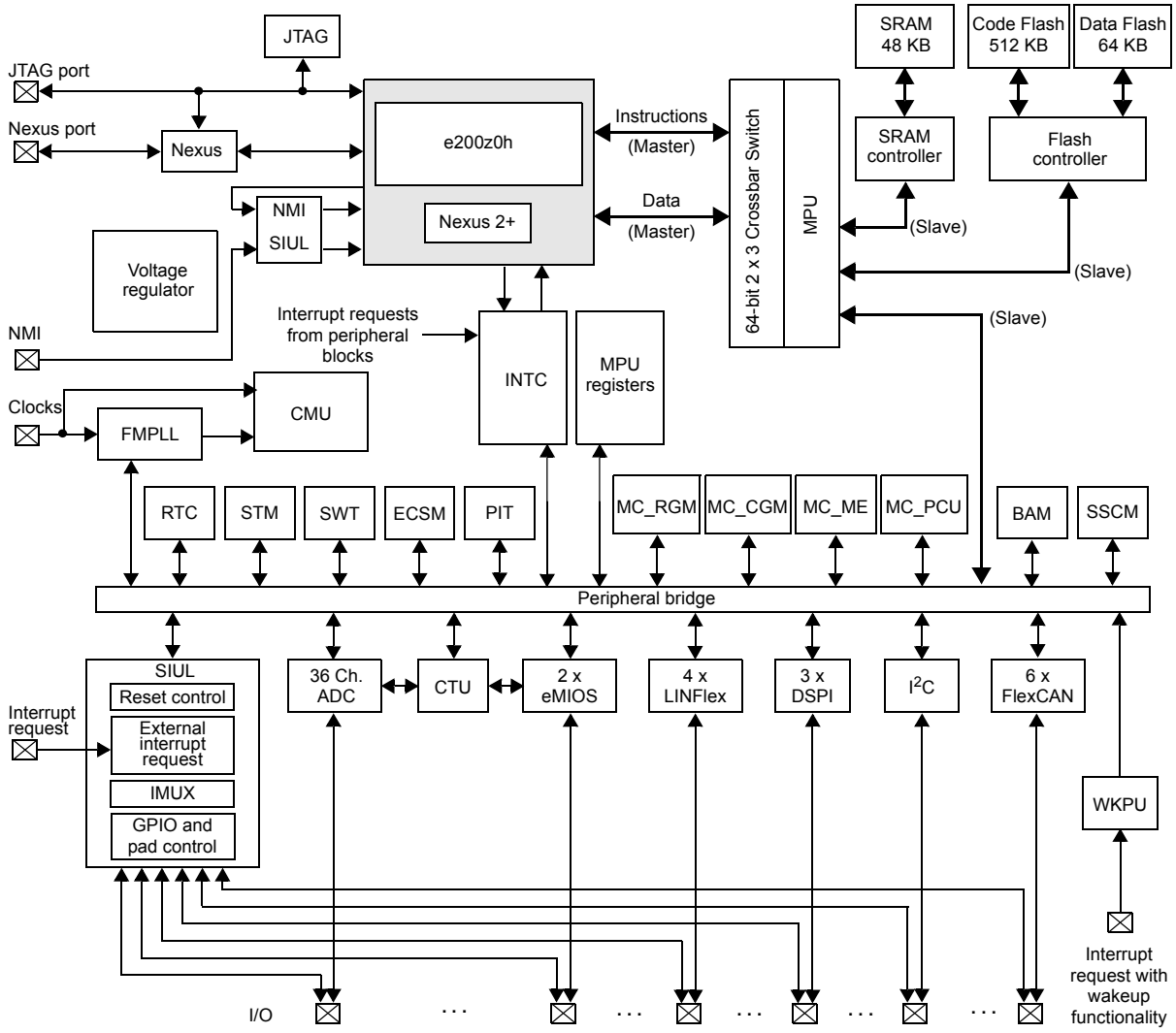
1.2 Description

The MPC5604B/C is a family of next generation microcontrollers built on the Power Architecture® embedded category.

The MPC5604B/C family of 32-bit microcontrollers is the latest achievement in integrated automotive application controllers. It belongs to an expanding family of automotive-focused products designed to address the next wave of body electronics applications within the vehicle. The advanced and cost-efficient host processor core of this automotive controller family complies with the Power Architecture embedded category and only implements the VLE (variable-length encoding) APU, providing improved code density. It operates at speeds of up to 64 MHz and offers high performance processing optimized for low power consumption. It capitalizes on the available development infrastructure of current Power Architecture devices and is supported with software drivers, operating systems and configuration code to assist with users implementations.

2 Block diagram

Figure 1 shows a top-level block diagram of the MPC5604B/C device series.



Legend:

ADC	Analog-to-Digital Converter
BAM	Boot Assist Module
FlexCAN	Controller Area Network
CMU	Clock Monitor Unit
CTU	Cross Triggering Unit
DSPI	Deserial Serial Peripheral Interface
eMIOS	Enhanced Modular Input Output System
FMPLL	Frequency-Modulated Phase-Locked Loop
I^2C	Inter-integrated Circuit Bus
IMUX	Internal Multiplexer
INTC	Interrupt Controller
JTAG	JTAG controller
LINFlex	Serial Communication Interface (LIN support)
ECSM	Error Correction Status Module
MC_CGM	Clock Generation Module
MC_ME	Mode Entry Module
MC_PCU	Power Control Unit
MC_RGM	Reset Generation Module
MPU	Memory Protection Unit
Nexus	Nexus Development Interface (NDI) Level
NMI	Non-Maskable Interrupt
PIT	Periodic Interrupt Timer
RTC	Real-Time Clock
SIUL	System Integration Unit Lite
SRAM	Static Random-Access Memory
SSCM	System Status Configuration Module
STM	System Timer Module
SWT	Software Watchdog Timer
WKPU	Wakeup Unit

Figure 1. MPC5604B/C block diagram

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration	Pin number				
								MPC560xB 64 LQFP	MPC560xC 64 LQFP	100 LQFP	144 LQFP	208 MAPBGA[3]
PE[1]	PCR[65]	AF0 AF1 AF2 AF3	GPIO[65] E0UC[17] CAN5TX[11] —	SIUL eMIOS_0 FlexCAN_5 —	I/O I/O O —	M	Tristate	—	—	8	12	F4
PE[2]	PCR[66]	AF0 AF1 AF2 AF3 —	GPIO[66] E0UC[18] — — SIN_1	SIUL eMIOS_0 — — DSPI_1	I/O I/O — — I	M	Tristate	—	—	89	128	D7
PE[3]	PCR[67]	AF0 AF1 AF2 AF3	GPIO[67] E0UC[19] SOUT_1 —	SIUL eMIOS_0 DSPI_1 —	I/O I/O O —	M	Tristate	—	—	90	129	C7
PE[4]	PCR[68]	AF0 AF1 AF2 AF3 —	GPIO[68] E0UC[20] SCK_1 — EIRQ[9]	SIUL eMIOS_0 DSPI_1 — SIUL	I/O I/O I/O — I	M	Tristate	—	—	93	132	D6
PE[5]	PCR[69]	AF0 AF1 AF2 AF3	GPIO[69] E0UC[21] CS0_1 MA[2]	SIUL eMIOS_0 DSPI_1 ADC	I/O I/O I/O O	M	Tristate	—	—	94	133	C6
PE[6]	PCR[70]	AF0 AF1 AF2 AF3	GPIO[70] E0UC[22] CS3_0 MA[1]	SIUL eMIOS_0 DSPI_0 ADC	I/O I/O O O	M	Tristate	—	—	95	139	B5
PE[7]	PCR[71]	AF0 AF1 AF2 AF3	GPIO[71] E0UC[23] CS2_0 MA[0]	SIUL eMIOS_0 DSPI_0 ADC	I/O I/O O O	M	Tristate	—	—	96	140	C4
PE[8]	PCR[72]	AF0 AF1 AF2 AF3	GPIO[72] CAN2TX[12] E0UC[22] CAN3TX[11]	SIUL FlexCAN_2 eMIOS_0 FlexCAN_3	I/O O I/O O	M	Tristate	—	—	9	13	G2
PE[9]	PCR[73]	AF0 AF1 AF2 AF3 — — —	GPIO[73] — E0UC[23] — WKPU[7][4] CAN2RX[12] CAN3RX[11]	SIUL — eMIOS_0 — WKPU FlexCAN_2 FlexCAN_3	I/O — I/O — I I I	S	Tristate	—	—	10	14	G1

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration	Pin number				
								MPC560xB 64 LQFP	MPC560xC 64 LQFP	100 LQFP	144 LQFP	208 MAPBGA[3]
PE[10]	PCR[74]	AF0 AF1 AF2 AF3 —	GPIO[74] LIN3TX CS3_1 — EIRQ[10]	SIUL LINFlex_3 DSPI_1 — SIUL	I/O O O — I	S	Tristate	—	—	11	15	G3
PE[11]	PCR[75]	AF0 AF1 AF2 AF3 — —	GPIO[75] — CS4_1 — LIN3RX WKPU[14][4]	SIUL — DSPI_1 — LINFlex_3 WKPU	I/O — O — I I	S	Tristate	—	—	13	17	H2
PE[12]	PCR[76]	AF0 AF1 AF2 AF3 — —	GPIO[76] — E1UC[19][13] — SIN_2 EIRQ[11]	SIUL — eMIOS_1 — DSPI_2 SIUL	I/O — I/O — I I	S	Tristate	—	—	76	109	C14
PE[13]	PCR[77]	AF0 AF1 AF2 AF3	GPIO[77] SOUT2 E1UC[20] —	SIUL DSPI_2 eMIOS_1 —	I/O O I/O —	S	Tristate	—	—	—	103	D15
PE[14]	PCR[78]	AF0 AF1 AF2 AF3 —	GPIO[78] SCK_2 E1UC[21] — EIRQ[12]	SIUL DSPI_2 eMIOS_1 — SIUL	I/O I/O I/O — I	S	Tristate	—	—	—	112	C13
PE[15]	PCR[79]	AF0 AF1 AF2 AF3	GPIO[79] CS0_2 E1UC[22] —	SIUL DSPI_2 eMIOS_1 —	I/O I/O I/O —	M	Tristate	—	—	—	113	A13
PF[0]	PCR[80]	AF0 AF1 AF2 AF3 —	GPIO[80] E0UC[10] CS3_1 — ANS[8]	SIUL eMIOS_0 DSPI_1 — ADC	I/O I/O O — I	J	Tristate	—	—	—	55	N10
PF[1]	PCR[81]	AF0 AF1 AF2 AF3 —	GPIO[81] E0UC[11] CS4_1 — ANS[9]	SIUL eMIOS_0 DSPI_1 — I	I/O I/O O — I	J	Tristate	—	—	—	56	P10

[1] Default manufacturing value is ‘1’. Value can be programmed by customer in Shadow Flash.

3.11.2 NVUSRO[OSCILLATOR_MARGIN] field description

The fast external crystal oscillator consumption is dependent on the OSCILLATOR_MARGIN bit value. Table 10 shows how NVUSRO[OSCILLATOR_MARGIN] controls the device configuration.

Table 10. OSCILLATOR_MARGIN field description

Value[1]	Description
0	Low consumption configuration (4 MHz/8 MHz)
1	High margin configuration (4 MHz/16 MHz)

[1] Default manufacturing value is ‘1’. Value can be programmed by customer in Shadow Flash.

3.11.3 NVUSRO[WATCHDOG_EN] field description

The watchdog enable/disable configuration after reset is dependent on the WATCHDOG_EN bit value. Table 11 shows how NVUSRO[WATCHDOG_EN] controls the device configuration.

Table 11. WATCHDOG_EN field description

Value[1]	Description
0	Disable after reset
1	Enable after reset

[1] Default manufacturing value is ‘1’. Value can be programmed by customer in Shadow Flash.

3.14 Thermal characteristics

3.14.1 Package thermal characteristics

Table 15. LQFP thermal characteristics[1]

Symbol		C	Parameter	Conditions[2]	Pin count	Value	Unit
$R_{\theta JA}$	CC	D	Thermal resistance, junction-to-ambient natural convection[3]	Single-layer board - 1s	64	60	°C/W
					100	64	
					144	64	
				Four-layer board - 2s2p	64	42	
					100	51	
					144	49	
$R_{\theta JB}$	CC	D	Thermal resistance, junction-to-board[4]	Single-layer board - 1s	64	24	°C/W
					100	36	
					144	37	
				Four-layer board - 2s2p	64	24	
					100	34	
					144	35	
$R_{\theta JC}$	CC	D	Thermal resistance, junction-to-case[5]	Single-layer board - 1s	64	11	°C/W
					100	22	
					144	22	
				Four-layer board - 2s2p	64	11	
					100	22	
					144	22	
Ψ_{JB}	CC	D	Junction-to-board thermal characterization parameter, natural convection	Single-layer board - 1s	64	TBD	°C/W
					100	33	
					144	34	
				Four-layer board - 2s2p	64	TBD	
					100	34	
					144	35	
Ψ_{JC}	CC	D	Junction-to-case thermal characterization parameter, natural convection	Single-layer board - 1s	64	TBD	°C/W
					100	9	
					144	10	
				Four-layer board - 2s2p	64	TBD	
					100	9	
					144	10	

[1] Thermal characteristics are based on simulation.

[2] C_L includes device and package capacitances (C_{PKG} < 5 pF).

3.15.5 I/O pad current specification

The I/O pads are distributed across the I/O supply segment. Each I/O supply segment is associated to a V_{DD}/V_{SS} supply pair as described in Table 22.

Table 22. I/O supply segment

Package	Supply segment					
	1	2	3	4	5	6
208 MAPBGA[1]	Equivalent to 144 LQFP segment pad distribution				MCKO	MDOn/MSEO
144 LQFP	pin20–pin49	pin51–pin99	pin100–pin122	pin 123–pin19	—	—
100 LQFP	pin16–pin35	pin37–pin69	pin70–pin83	pin 84–pin15	—	—
64 LQFP	pin8–pin26	pin28–pin55	pin56–pin7	—	—	—

[1] 208 MAPBGA available only as development package for Nexus2+

Table 23 provides I/O consumption figures.

In order to ensure device reliability, the average current of the I/O on a single segment should remain below the I_{AVGSEG} maximum value.

Table 23. I/O consumption

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
I_{SWTSLW}[2]	CC	D	Dynamic I/O current for SLOW configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	20	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	16	
I_{SWTMED}[2]	CC	D	Dynamic I/O current for MEDIUM configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	29	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	17	
I_{SWTFST}[2]	CC	D	Dynamic I/O current for FAST configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	110	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	50	
I_{RMSSLW}	CC	D	Root mean square I/O current for SLOW configuration	C_L = 25 pF, 2 MHz	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	2.3	mA
				C_L = 25 pF, 4 MHz		—	—	3.2	
				C_L = 100 pF, 2 MHz		—	—	6.6	
				C_L = 25 pF, 2 MHz	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	1.6	
				C_L = 25 pF, 4 MHz		—	—	2.3	
				C_L = 100 pF, 2 MHz		—	—	4.7	

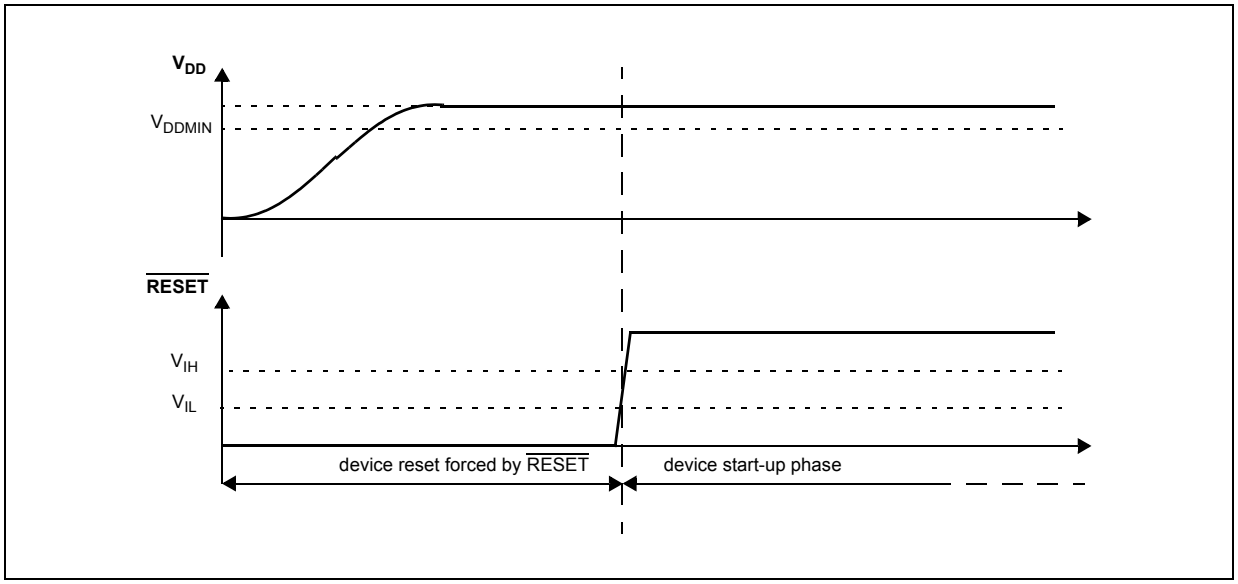


Figure 8. Start-up reset requirements

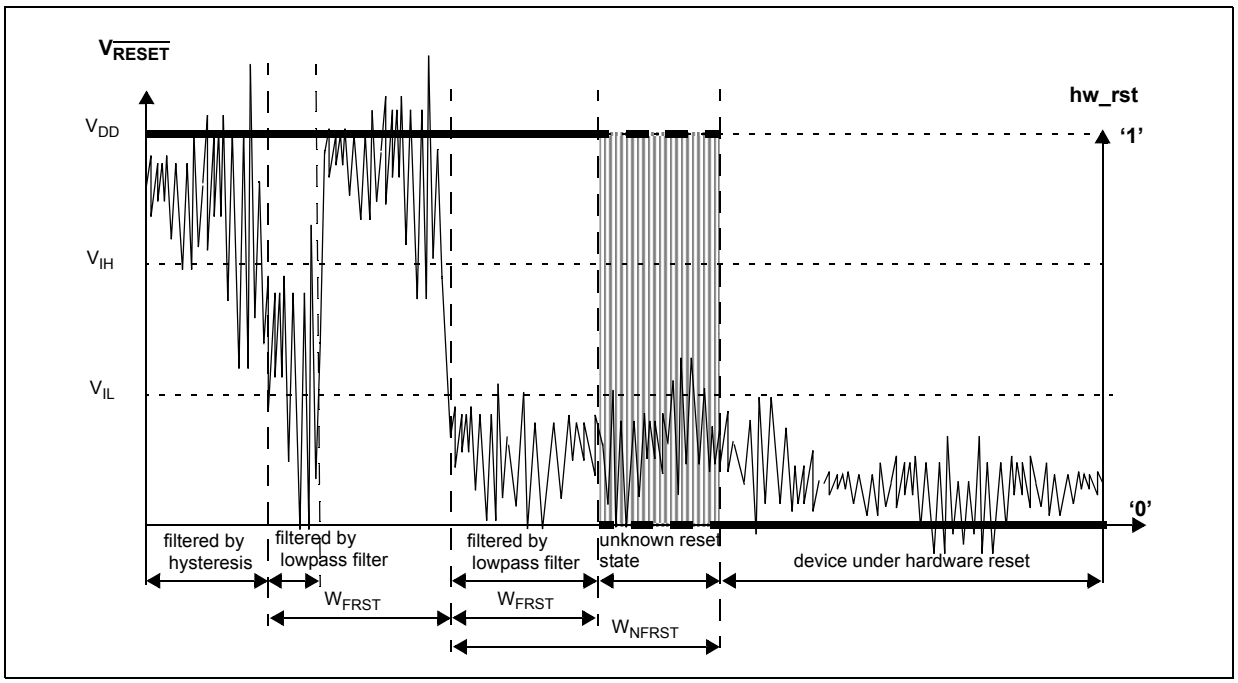


Figure 9. Noise filtering on reset signal

Table 25. Reset electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
V_{IH}	SR	P	Input High Level CMOS (Schmitt Trigger)	—	$0.65V_{DD}$	—	$V_{DD}+0.4$	V

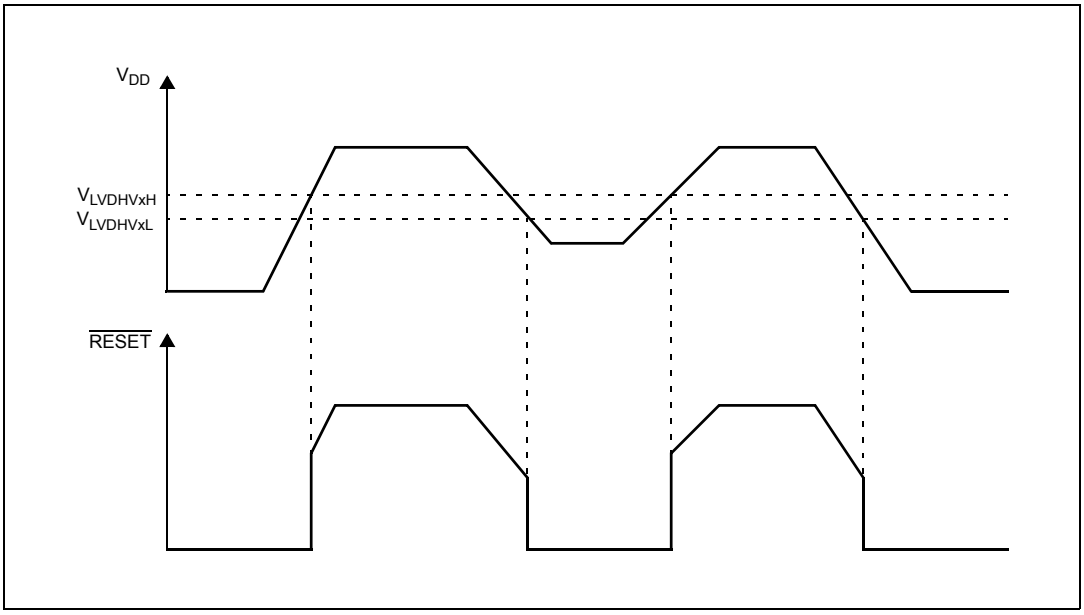


Figure 13. Low voltage detector vs reset

Table 27. Low voltage detector electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
V_{PORUP}	SR	P	Supply for functional POR module	—	1.0	—	5.5	V
V_{PORH}	CC	P	Power-on reset threshold	T_A = 25 °C, after trimming	1.5	—	2.6	
		T		—	1.5	—	2.6	
$V_{LVDHV3H}$	CC	T	LVDHV3 low voltage detector high threshold	—	—	—	2.95	
$V_{LVDHV3L}$	CC	P	LVDHV3 low voltage detector low threshold		2.6	—	2.9	
$V_{LVDHV5H}$	CC	T	LVDHV5 low voltage detector high threshold		—	—	4.5	
$V_{LVDHV5L}$	CC	P	LVDHV5 low voltage detector low threshold		3.8	—	4.4	
$V_{LVDLVCORL}$	CC	P	LVDLVCOR low voltage detector low threshold		1.08	—	1.16	
$V_{LVDLVBKPL}$	CC	P	LVDLVBKP low voltage detector low threshold		1.08	—	1.16	

[1] V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

3.18 Power consumption

Table 28 provides DC electrical characteristics for significant application modes. These values are indicative values; actual consumption depends on the application.

6 Data Flash Power Down. Code Flash in Low Power. SIRC (128 kHz) and FIRC (16 MHz) on. 10 MHz XTAL clock. FlexCAN: instances: 0, 1, 2 ON (clocked but not reception or transmission), instances: 4, 5, 6 clock gated. LINFlex: instances: 0, 1, 2 ON (clocked but not reception or transmission), instance: 3 clock gated. eMIOS: instance: 0 ON (16 channels on PA[0]–PA[11] and PC[12]–PC[15]) with PWM 20 kHz, instance: 1 clock gated. DSPI: instance: 0 (clocked but no communication). RTC/API ON. PIT ON. STM ON. ADC ON but not conversion except 2 analog watchdog.

7 Only for the “P” classification: No clock, FIRC (16 MHz) off, SIRC (128 kHz) on, PLL off, HPvreg off, ULPVreg/LPVreg on. All possible peripherals off and clock gated. Flash in power down mode.

8 When going from RUN to STOP mode and the core consumption is > 6 mA, it is normal operation for the main regulator module to be kept on by the on-chip current monitoring circuit. This is most likely to occur with junction temperatures exceeding 125 °C and under these circumstances, it is possible for the current to initially exceed the maximum STOP specification by up to 2 mA. After entering stop, the application junction temperature will reduce to the ambient level and the main regulator will be automatically switched off when the load current is below 6 mA.

9 Only for the “P” classification: ULPreg on, HP/LPVreg off, 32 KB RAM on, device configured for minimum consumption, all possible modules switched off.

10 ULPreg on, HP/LPVreg off, 8 KB RAM on, device configured for minimum consumption, all possible modules switched off.

3.19 Flash memory electrical characteristics

3.19.1 Program/Erase characteristics

Table 29 shows the program and erase characteristics.

Table 29. Program and erase specifications

Symbol		C	Parameter	Value				Unit
				Min	Typ[1]	Initial max[2]	Max[3]	
$T_{dwprogram}$	CC	C	Double word (64 bits) program time[4]	—	22	50	500	µs
$T_{16Kpperase}$			16 KB block preprogram and erase time	—	300	500	5000	ms
$T_{32Kpperase}$			32 KB block preprogram and erase time	—	400	600	5000	ms
$T_{128Kpperase}$			128 KB block preprogram and erase time	—	800	1300	7500	ms
T_{esus}	CC	D	Erase suspend latency	—	—	30	30	µs

1 Typical program and erase times assume nominal supply values and operation at 25 °C.

2 Initial factory condition: < 100 program/erase cycles, 25 °C, typical supply voltage.

3 The maximum program and erase times occur after the specified number of program/erase cycles. These maximum values are characterized but not guaranteed.

4 Actual hardware programming times. This does not include software overhead.

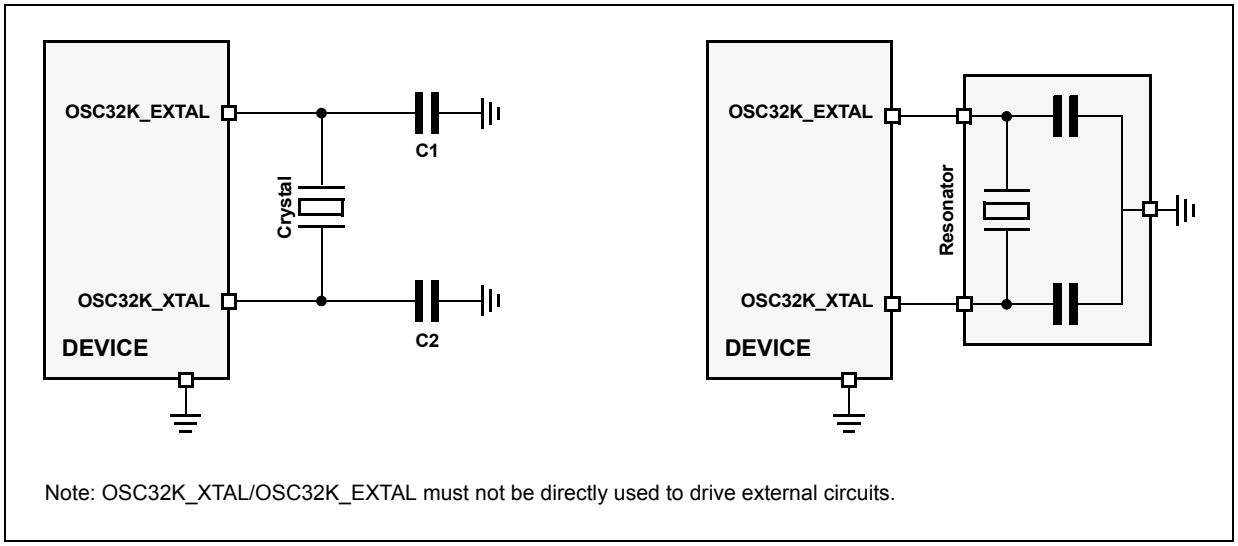


Figure 16. Crystal oscillator and resonator connection scheme

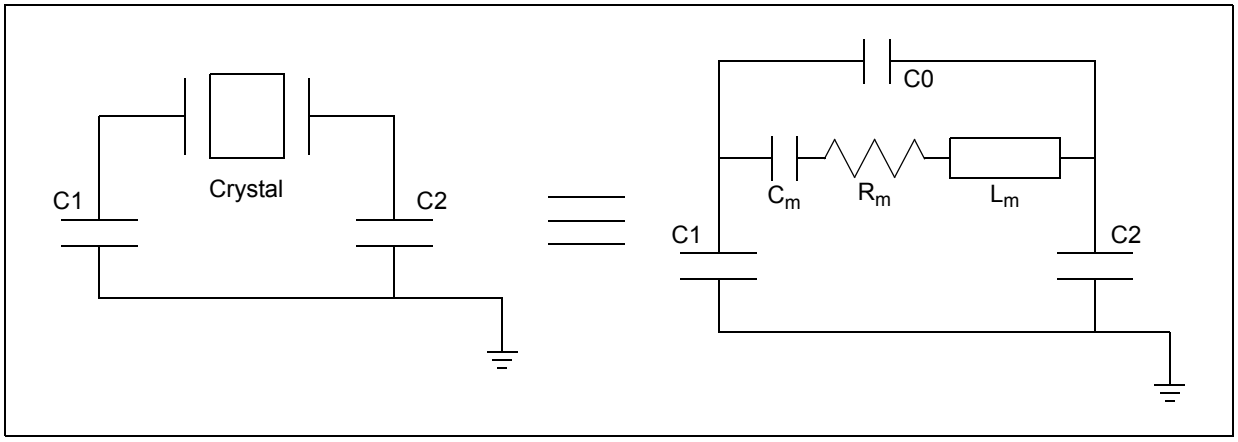


Figure 17. Equivalent circuit of a quartz crystal

Table 39. Crystal motional characteristics[1]

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
L_m	Motional inductance	—	—	11.796	—	KH
C_m	Motional capacitance	—	—	2	—	fF
C1/C2	Load capacitance at OSC32K_XTAL and OSC32K_EXTAL with respect to ground[2]	—	18	—	28	pF
R_m[3]	Motional resistance	AC coupled @ C0 = 2.85 pF[4]	—	—	65	kΩ
		AC coupled @ C0 = 4.9 pF[4]	—	—	50	
		AC coupled @ C0 = 7.0 pF[4]	—	—	35	
		AC coupled @ C0 = 9.0 pF[4]	—	—	30	

[1] Crystal used: Epson Toyocom MC306

possible, ideally infinite. This capacitor contributes to attenuating the noise present on the input pin; furthermore, it sources charge during the sampling phase, when the analog signal source is a high-impedance source.

A real filter can typically be obtained by using a series resistance with a capacitor on the input pin (simple RC filter). The RC filtering may be limited according to the value of source impedance of the transducer or circuit supplying the analog signal to be measured. The filter at the input pins must be designed taking into account the dynamic characteristics of the input signal (bandwidth) and the equivalent input impedance of the ADC itself.

In fact a current sink contributor is represented by the charge sharing effects with the sampling capacitance: being C_S and C_{p2} substantially two switched capacitances, with a frequency equal to the conversion rate of the ADC, it can be seen as a resistive path to ground. For instance, assuming a conversion rate of 1 MHz, with C_S+C_{p2} equal to 3 pF, a resistance of 330 kΩ is obtained ($R_{EQ} = 1 / (f_c \times (C_S+C_{p2}))$, where f_c represents the conversion rate at the considered channel). To minimize the error induced by the voltage partitioning between this resistance (sampled voltage on C_S+C_{p2}) and the sum of $R_S + R_F$, the external circuit must be designed to respect the Equation 4:

Eqn. 4

$$V_A \bullet \frac{R_S + R_F}{R_{EQ}} < \frac{1}{2} LSB$$

Equation 4 generates a constraint for external network design, in particular on a resistive path.

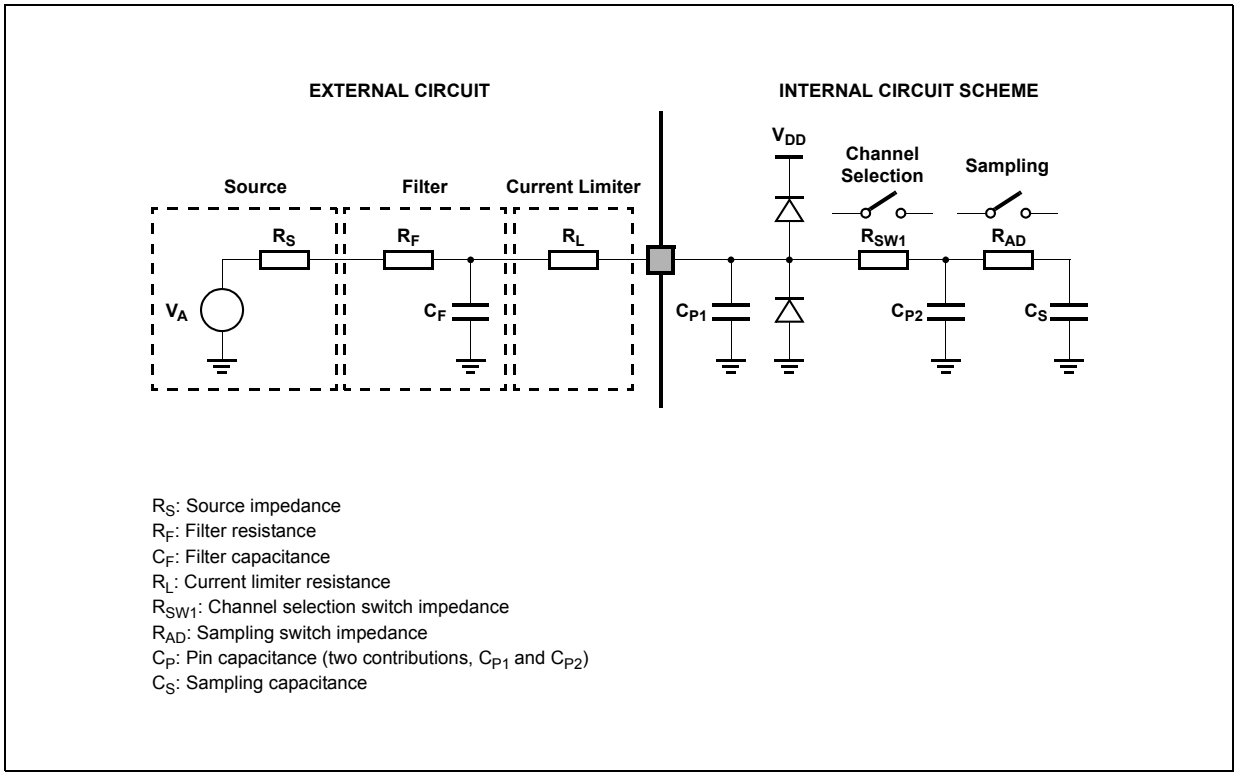


Figure 20. Input equivalent circuit (precise channels)

1. A first and quick charge transfer from the internal capacitance C_{P1} and C_{P2} to the sampling capacitance C_S occurs (C_S is supposed initially completely discharged): considering a worst case (since the time constant in reality would be faster) in which C_{P2} is reported in parallel to C_{P1} (call $C_P = C_{P1} + C_{P2}$), the two capacitances C_P and C_S are in series, and the time constant is

Eqn. 5

$$\tau_1 = (R_{SW} + R_{AD}) \bullet \frac{C_P \bullet C_S}{C_P + C_S}$$

Equation 5 can again be simplified considering only C_S as an additional worst condition. In reality, the transient is faster, but the A/D converter circuitry has been designed to be robust also in the very worst case: the sampling time t_s is always much longer than the internal time constant:

Eqn. 6

$$\tau_1 < (R_{SW} + R_{AD}) \bullet C_S \ll t_s$$

The charge of C_{P1} and C_{P2} is redistributed also on C_S, determining a new value of the voltage V_{A1} on the capacitance according to Equation 7:

Eqn. 7

$$V_{A1} \bullet (C_S + C_{P1} + C_{P2}) = V_A \bullet (C_{P1} + C_{P2})$$

2. A second charge transfer involves also C_F (that is typically bigger than the on-chip capacitance) through the resistance R_L: again considering the worst case in which C_{P2} and C_S were in parallel to C_{P1} (since the time constant in reality would be faster), the time constant is:

Eqn. 8

$$\tau_2 < R_L \bullet (C_S + C_{P1} + C_{P2})$$

In this case, the time constant depends on the external circuit: in particular imposing that the transient is completed well before the end of sampling time t_s, a constraints on R_L sizing is obtained:

Eqn. 9

$$8.5 \bullet \tau_2 = 8.5 \bullet R_L \bullet (C_S + C_{P1} + C_{P2}) < t_s$$

Of course, R_L shall be sized also according to the current limitation constraints, in combination with R_S (source impedance) and R_F (filter resistance). Being C_F definitively bigger than C_{P1}, C_{P2} and C_S, then the final voltage V_{A2} (at the end of the charge transfer transient) will be much higher than V_{A1}. Equation 10 must be respected (charge balance assuming now C_S already charged at V_{A1}):

Eqn. 10

$$V_{A2} \bullet (C_S + C_{P1} + C_{P2} + C_F) = V_A \bullet C_F + V_{A1} \bullet (C_{P1} + C_{P2} + C_S)$$

The two transients above are not influenced by the voltage source that, due to the presence of the $R_F C_F$ filter, is not able to provide the extra charge to compensate the voltage drop on C_S with respect to the ideal source V_A; the time constant $R_F C_F$ of the filter is very high with respect to the sampling time (t_s). The filter is typically designed to act as anti-aliasing.

Table 45. ADC conversion characteristics (continued)

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
C_{P3}	CC	D	ADC input pin capacitance 3	—		—	—	1	pF
R_{SW1}	CC	D	Internal resistance of analog source	—		—	—	3	kΩ
R_{SW2}	CC	D	Internal resistance of analog source	—		—	—	2	kΩ
R_{AD}	CC	D	Internal resistance of analog source	—		—	—	2	kΩ
I_{INJ}	SR	—	Input current Injection	Current injection on one ADC input, different from the converted one	V_{DD} = 3.3 V ± 10%	–5	—	5	mA
					V_{DD} = 5.0 V ± 10%	–5	—	5	
| INL |	CC	T	Absolute value for integral non-linearity	No overload		—	0.5	1.5	LSB
| DNL |	CC	T	Absolute differential non-linearity	No overload		—	0.5	1.0	LSB
$\| E_O \|$	CC	T	Absolute offset error	—		—	0.5	—	LSB
$\| E_G \|$	CC	T	Absolute gain error	—		—	0.6	—	LSB
TUEp	CC	P	Total unadjusted error[7] for precise channels, input only pins	Without current injection		–2	0.6	2	LSB
		T		With current injection		–3		3	
TUEx	CC	T	Total unadjusted error[7] for extended channel	Without current injection		–3	1	3	LSB
		T		With current injection		–4		4	

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.

2 Analog and digital V_{SS} **must** be common (to be tied together externally).

3 V_{AINx} may exceed V_{SS_ADC} and V_{DD_ADC} limits, remaining on absolute maximum ratings, but the results of the conversion will be clamped respectively to 0x000 or 0x3FF.

4 Duty cycle is ensured by using system clock without prescaling. When ADCLKSEL = 0, the duty cycle is ensured by internal divider by 2.

5 During the sampling time the input capacitance C_S can be charged/discharged by the external source. The internal resistance of the analog source must allow the capacitance to reach its final voltage level within t_s. After the end of the sampling time t_s, changes of the analog input voltage have no effect on the conversion result. Values for the sample clock t_s depend on programming.

6 This parameter does not include the sampling time t_s, but only the time for determining the digital result and the time to load the result's register with the conversion result.

7 Total Unadjusted Error: The maximum error that occurs without adjusting Offset and Gain errors. This error is a combination of Offset, Gain and Integral Linearity errors.

Table 47. DSPI characteristics[1] (continued)

No.	Symbol		C	Parameter		DSPI0/DSPI1			DSPI2			Unit
						Min	Typ	Max	Min	Typ	Max	
10	t_{HI}	SR	D	Data hold time for inputs	Master mode	0	—	—	0	—	—	ns
					Slave mode	2^6	—	—	2^6	—	—	
11	t_{SUO}[7]	CC	D	Data valid after SCK edge	Master mode	—	—	32	—	—	50	ns
					Slave mode	—	—	52	—	—	160	
12	t_{HO}[7]	CC	D	Data hold time for outputs	Master mode	0	—	—	0	—	—	ns
					Slave mode	8	—	—	13	—	—	

1 Operating conditions: C_L = 10 to 50 pF, $Slew_{IN}$ = 3.5 to 15 ns.

2 Maximum value is reached when CSn pad is configured as SLOW pad while SCK pad is configured as MEDIUM. A positive value means that SCK starts before CSn is asserted. DSPI2 has only SLOW SCK available.

3 Maximum value is reached when CSn pad is configured as MEDIUM pad while SCK pad is configured as SLOW. A positive value means that CSn is deasserted before SCK. DSPI0 and DSPI1 have only MEDIUM SCK available.

4 The t_{CSC} delay value is configurable through a register. When configuring t_{CSC} (using PCSSCK and CSSCK fields in DSPI_CTARx registers), delay between internal CS and internal SCK must be higher than Δt_{CSC} to ensure positive t_{CSCext}.

5 The t_{ASC} delay value is configurable through a register. When configuring t_{ASC} (using PASC and ASC fields in DSPI_CTARx registers), delay between internal CS and internal SCK must be higher than Δt_{ASC} to ensure positive t_{ASCext}.

6 This delay value corresponds to SMPL_PT = 00b which is bit field 9 and 8 of the DSPI_MCR.

7 SCK and SOUT configured as MEDIUM pad

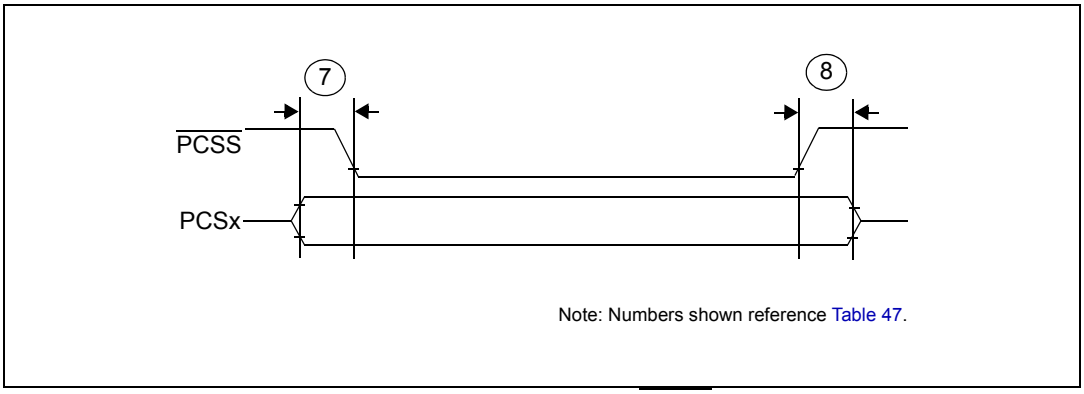


Figure 32. DSPI PCS strobe (PCSS) timing

3.27.3 Nexus characteristics

Table 48. Nexus characteristics

No.	Symbol		C	Parameter	Value			Unit
					Min	Typ	Max	
1	t_{TCYC}	CC	D	TCK cycle time	64	—	—	ns
2	t_{MCYC}	CC	D	MCKO cycle time	32	—	—	ns
3	t_{MDOV}	CC	D	MCKO low to MDO data valid	—	—	8	ns
4	t_{MSEOV}	CC	D	MCKO low to MSEO_b data valid	—	—	8	ns
5	t_{EVTOV}	CC	D	MCKO low to EVTO data valid	—	—	8	ns
10	t_{NTDIS}	CC	D	TDI data setup time	15	—	—	ns
	t_{NTMSS}	CC	D	TMS data setup time	15	—	—	ns
11	t_{NTDIH}	CC	D	TDI data hold time	5	—	—	ns
	t_{NTMSH}	CC	D	TMS data hold time	5	—	—	ns
12	t_{TDOV}	CC	D	TCK low to TDO data valid	35	—	—	ns
13	t_{TDOI}	CC	D	TCK low to TDO data invalid	6	—	—	ns

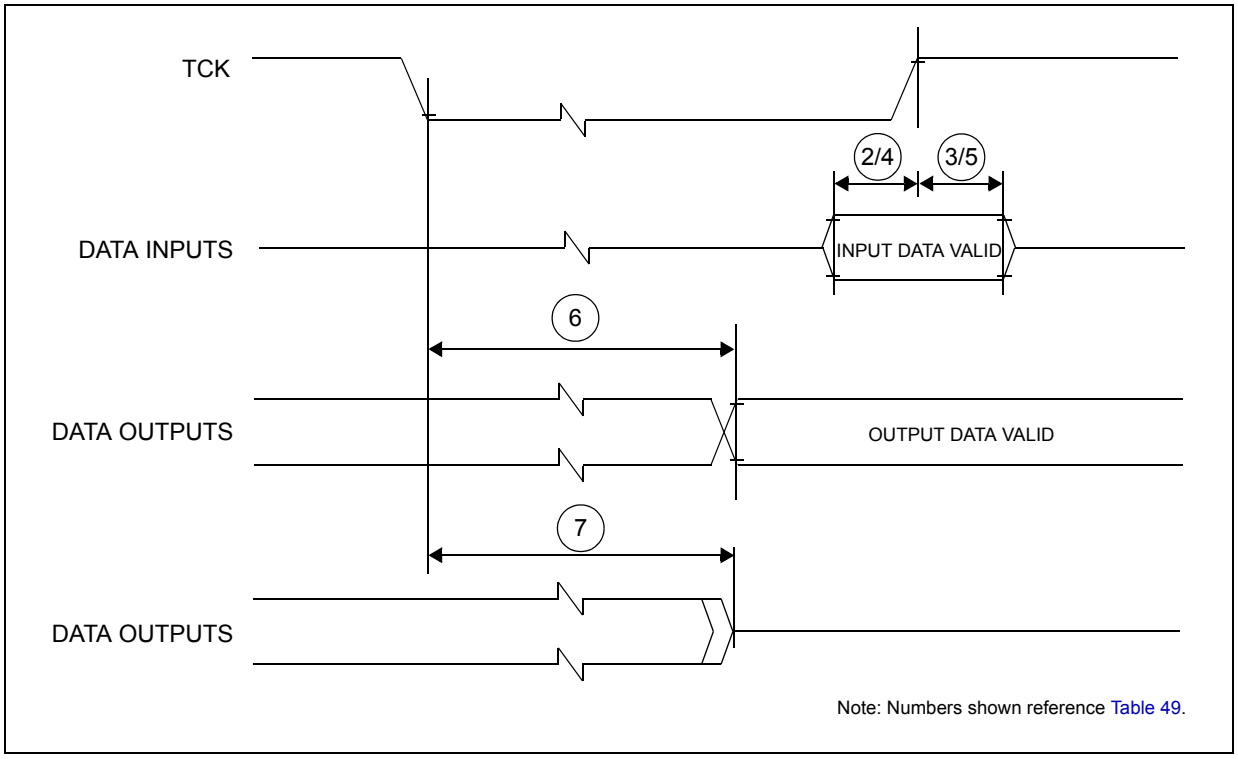


Figure 34. Timing diagram – JTAG boundary scan

4 Package characteristics

4.1 Package mechanical data

4.1.2 100 LQFP

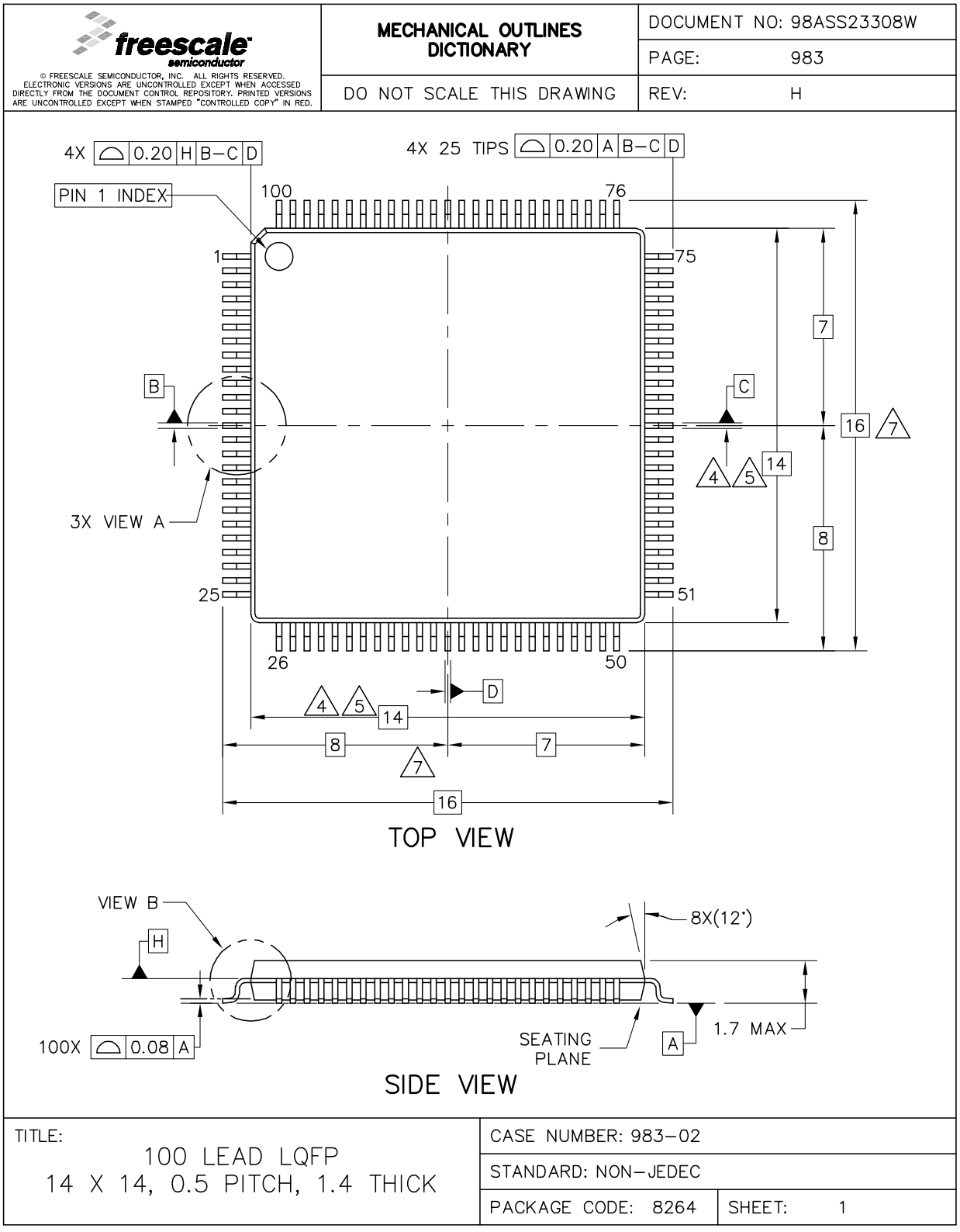


Figure 38. 100 LQFP package mechanical drawing (1 of 3)

Table 50. Revision history (continued)

Revision	Date	Description of Changes
10	15 Oct 2012	Table 1 (MPC5604B/C device comparison), added footnote for MPC5603BxLH and MPC5604BxLH about FlexCAN availability. Table 3 (MPC5604B/C series block summary), replaced “System watchdog timer” with “Software watchdog timer” and specified AUTOSAR (Automotive Open System Architecture) Table 6 (Functional port pin descriptions): replaced footnote “Available only on MPC560xC versions and MPC5604B 208 MAPBGA devices” with “Available only on MPC560xC versions, MPC5603B 64 LQFP, MPC5604B 64 LQFP and MPC5604B 208 MAPBGA devices”, replaced VDD with VDD_HV Figure 10 (Voltage regulator capacitance connection), updated pin name apperence Renamed Figure 11 (V_{DD_HV} and V_{DD_BV} maximum slope) (was “VDD and VDD_BV maximum slope”) Renamed Figure 12 (V_{DD_HV} and V_{DD_BV} supply constraints during STANDBY mode exit) (was “VDD and VDD_BV supply constraints during STANDBY mode exit”) Table 13 (Recommended operating conditions (3.3 V)), added minimum value of T_{VDD} and footnote about it. Table 14 (Recommended operating conditions (5.0 V)), added minimum value of T_{VDD} and footnote about it. Section 3.17.1, “Voltage regulator electrical characteristics: replaced “slew rate of V_{DD}/V_{DD_BV}” with “slew rate of both V_{DD_HV} and V_{DD_BV}” replaced “When STANDBY mode is used, further constraints apply to the V_{DD}/V_{DD_BV} in order to guarantee correct regulator functionality during STANDBY exit.” with “When STANDBY mode is used, further constraints are applied to the both V_{DD_HV} and V_{DD_BV} in order to guarantee correct regulator function during STANDBY exit.” Table 28 (Power consumption on VDD_BV and VDD_HV), updated footnotes of I_{DDMAX} and I_{DDRUN} stating that both currents are drawn only from the V_{DD_BV} pin. Table 32 (Flash memory power supply DC electrical characteristics), in the paremeter column replaced V_{DD_BV} and V_{DD_HV} respectively with VDD_BV and VDD_HV. Table 46 (On-chip peripherals current consumption), in the paremeter column replaced V_{DD_BV}, V_{DD_HV} and $V_{DD\_HV\_ADC}$ respectively with VDD_BV, VDD_HV and VDD_HV_ADC Updated Section 3.26.2, “Input impedance and ADC accuracy Table 47 (DSPI characteristics), modified symbol for t_{PCSC} and t_{PASC}
11	14 Nov 2012	In the cover feature list: added “and ECC” at the end of “Up to 512 KB on-chip code flash supported with the flash controller” added “with ECC” at the end of “Up to 48 KB on-chip SRAM” Table 13 (Recommended operating conditions (3.3 V)), removed minimum value of T_{VDD} and relative footnote. Table 14 (Recommended operating conditions (5.0 V)), removed minimum value of T_{VDD} and relative footnote.

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